



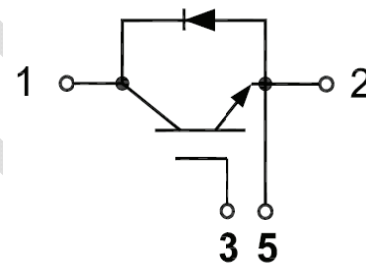
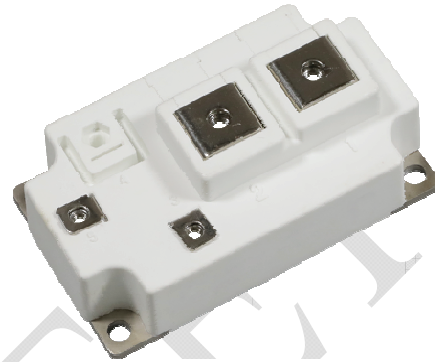
GT900SD120T2ZH

IGBT Module

Preliminary Data

Features:

- Field Stop Trench Gate IGBT
- Short Circuit Rated >10 μ s
- Low Saturation Voltage
- Low Switching Loss
- 100% RBSOA Tested(2 \times I_c)
- Low Stray Inductance
- Lead Free, Compliant with RoHS Requirement



Applications:

- Induction Heating
- UPS Systems
- High Power converters

IGBT, Inverter Maximum Rated Values of IGBT

V _{CES}	Collector-Emitter Blocking Voltage	T _J =25°C	1200	V
V _{GES}	Gate-Emitter Voltage		±20	V
I _C	Continuous Collector Current	T _C =100°C	900	A
		T _C =25°C	1670	A
I _{CM}	Peak Collector Current Repetitive	t _p =1ms	1800	A
t _{SC}	Short Circuit Withstand Time		>10	μs
P _D	Maximum Power Dissipation (IGBT)	T _C =25°C T _{Jmax} =175°C	6000	W



Electrical Characteristics of IGBT

Static Characteristics

Symbol	Description	Conditions	Min	Typ	Max	Unit
$V_{GE(th)}$	Gate-Emitter Threshold Voltage	$I_C=1\text{ mA}, V_{CE}=V_{GE}, T_J=25^\circ\text{C}$	5.0	5.5	6.0	V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=900\text{A}, V_{GE}=15\text{V}$	$T_J=25^\circ\text{C}$	1.80	2.00	V
			$T_J=125^\circ\text{C}$	2.10	2.30	V
I_{CES}	Collector-Emitter Leakage Current	$V_{GE}=0\text{V}, V_{CE}=V_{CES}, T_J=25^\circ\text{C}$			1	mA
I_{GES}	Gate-Emitter Leakage Current	$V_{GE}=\pm 20\text{V}, V_{CE}=0\text{V}, T_J=25^\circ\text{C}$			400	nA
C_{ies}	Input Capacitance	$V_{CE}=25\text{V}, V_{GE}=0\text{V}, f=1\text{MHz}, T_J=25^\circ\text{C}$		55.2		nF
C_{oes}	Output capacitance			3.0		nF

Switching Characteristics

$t_{d(on)}$	Turn-on Delay Time	$V_{CC}=600\text{V}, I_C=900\text{A}, R_{Gon}=2.5\Omega, V_{GE}=\pm 15\text{V},$ Inductive Load	$T_J=25^\circ\text{C}$	2250		ns
			$T_J=125^\circ\text{C}$	1950		
t_r	Rise Time	$V_{CC}=600\text{V}, I_C=900\text{A}, R_{Gon}=2.5\Omega, V_{GE}=\pm 15\text{V},$ Inductive Load	$T_J=25^\circ\text{C}$	360		ns
			$T_J=125^\circ\text{C}$	420		
$t_{d(off)}$	Turn-off Delay Time	$V_{CC}=600\text{V}, I_C=900\text{A}, R_{Goff}=2.5\Omega, V_{GE}=\pm 15\text{V},$ Inductive Load	$T_J=25^\circ\text{C}$	1965		ns
			$T_J=125^\circ\text{C}$	2100		
t_f	Fall Time	$V_{CC}=600\text{V}, I_C=900\text{A}, R_{Goff}=2.5\Omega, V_{GE}=\pm 15\text{V},$ Inductive Load	$T_J=25^\circ\text{C}$	180		ns
			$T_J=125^\circ\text{C}$	195		
E_{on}	Turn-on Switching Loss	$V_{CC}=600\text{V}, I_C=900\text{A}, R_{Gon}=2.5\Omega, V_{GE}=\pm 15\text{V},$ $di/dt=2250\text{A}/\mu\text{s} (T_J=125^\circ\text{C})$ Inductive Load	$T_J=25^\circ\text{C}$	70.2		mJ
			$T_J=125^\circ\text{C}$	110		
E_{off}	Turn-off Switching Loss	$V_{CC}=600\text{V}, I_C=900\text{A}, R_{Goff}=2.5\Omega, V_{GE}=\pm 15\text{V},$ $du/dt=3450\text{V}/\mu\text{s} (T_J=125^\circ\text{C})$ Inductive Load	$T_J=25^\circ\text{C}$	90		mJ
			$T_J=125^\circ\text{C}$	128		
Q_g	Total Gate Charge	$V_{GE}=+15\text{V} \dots -15\text{V}$	$T_J=25^\circ\text{C}$	7470		nC
RBSOA	$I_C=1800\text{A}, V_{CC}=1050\text{V}, V_p=1200\text{V}, R_g = 4.7\Omega, V_{GE}=+15\text{V to } 0\text{V}, T_J=150^\circ\text{C}$			Trapezoid		
SCSOA	$V_{CC} = 600\text{V}, V_{GE} = 15\text{V}, T_J=150^\circ\text{C}$			10		μs
$R_{\theta JC}$	IGBT Thermal Resistance: Junction-To-Case				0.025	$^\circ\text{C}/\text{W}$



Diode, Inverter Maximum Rated Values of Diode

V_{RRM}	Repetitive Peak Reverse Voltage	$T_J=25^{\circ}\text{C}$	1200	V
I_F	Diode Continuous Forward Current		900	A
I_{FM}	Peak FWD Current Repetitive	$t_p=1\text{ms}$	1800	A

Electrical Characteristics of Diode

Symbol	Description	Conditions	Min	Typ	Max	Unit
V_{FM}	Forward Voltage	$I_F=900\text{A}$	$T_J=25^{\circ}\text{C}$	2.2		V
			$T_J=125^{\circ}\text{C}$	2.4		
t_{rr}	Reverse Recovery Time		$T_J=25^{\circ}\text{C}$	0.41		μs
			$T_J=125^{\circ}\text{C}$	0.65		
I_{rr}	Peak Reverse Recovery Current	$I_F=900\text{A},$ $V_R=600\text{V},$ $V_{GE}=-15\text{V}$ $diF/dt=3200\text{A}/\mu\text{s}(T_J=125^{\circ}\text{C}),$	$T_J=25^{\circ}\text{C}$	286		A
			$T_J=125^{\circ}\text{C}$	354		
Q_{rr}	Reverse Recovery Charge		$T_J=25^{\circ}\text{C}$	62		μC
			$T_J=125^{\circ}\text{C}$	115		
E_{rec}	Reverse Recovery Energy		$T_J=25^{\circ}\text{C}$	26		mJ
			$T_J=125^{\circ}\text{C}$	46		
$R_{\theta JC}$	Diode Thermal Resistance: Junction-To-Case			0.043		$^{\circ}\text{C}/\text{W}$



Module

Symbol	Description	Min	Typ	Max	Unit
V_{iso}	Isolation Voltage (All Terminals Shorted)	RMS, f = 50Hz, 1minute	2.5		kV
L_{sCE}	Stray Inductance Module		16		nH
T_J	Maximum Junction Temperature			175	°C
T_{JOP}	Maximum Operating Junction Temperature Range	-40		+150	°C
T_{stg}	Storage Temperature	-40		+125	°C
CTI	Comparative Tracking Index	200			
$R_{\theta CS}$	Case-To-Sink Thermally (Conductive Grease Applied)		0.03		°C/W
T	Signal Terminals Screw:M4	1.1		2.0	N·m
	Power Terminals Screw:M6	2.5		5.0	N·m
T	Mounting Screw:M6	3.0		6.0	N·m
G	Weight		320		g

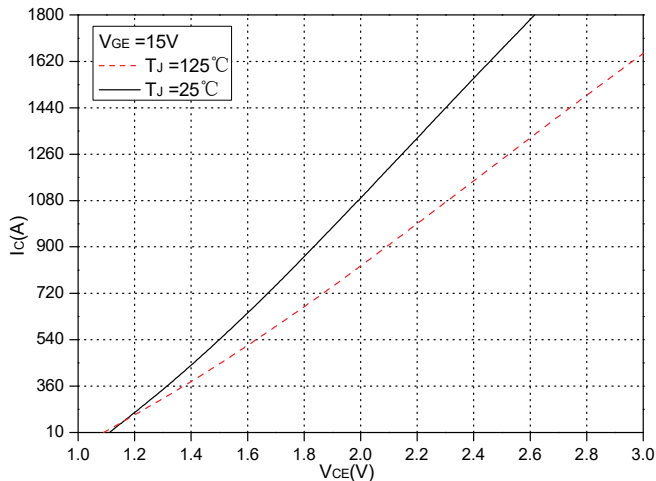


Fig.1 Typical Saturation Voltage Characteristics

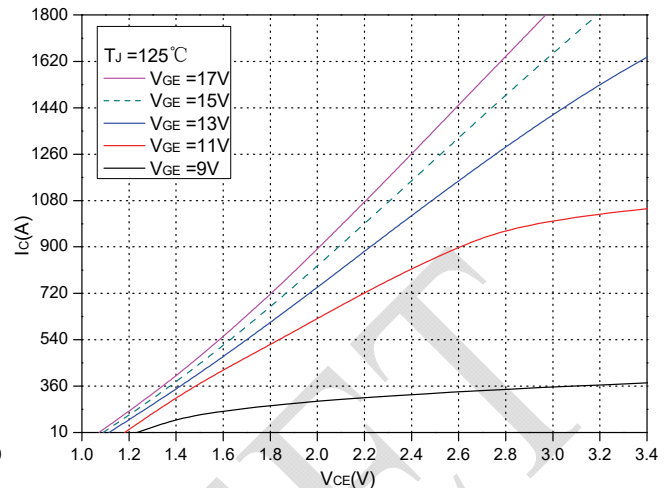


Fig.2 Typical Output Characteristics

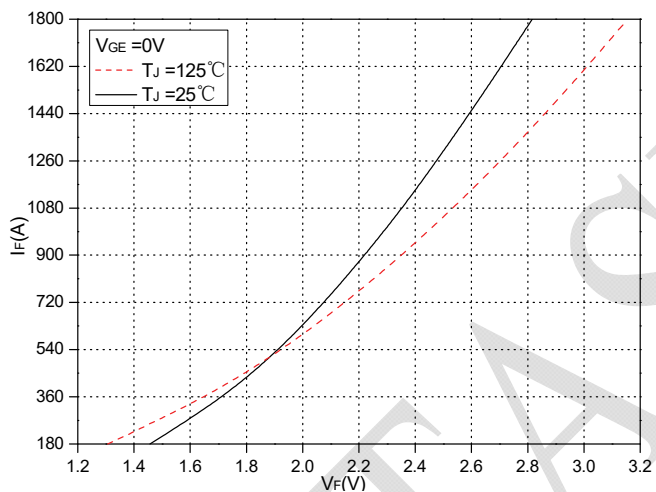


Fig.3 Forward Characteristics of FWD

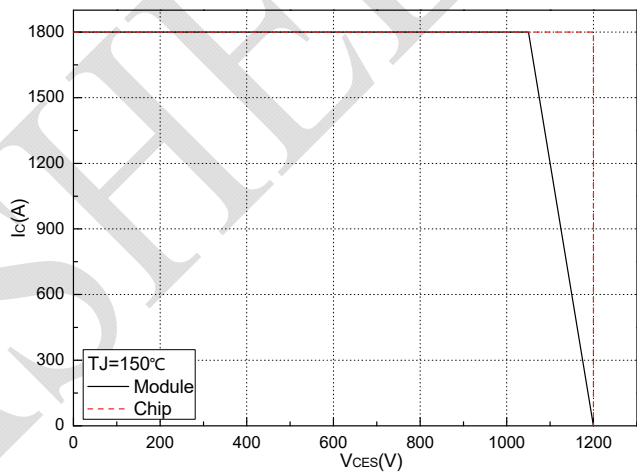


Fig.4 Reverse Bias Safe Operation Area (RBSOA)

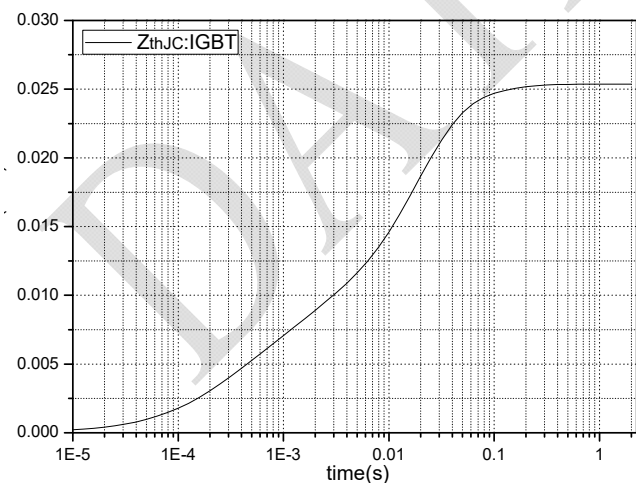


Fig.5 Transient Thermal Impedance (IGBT)

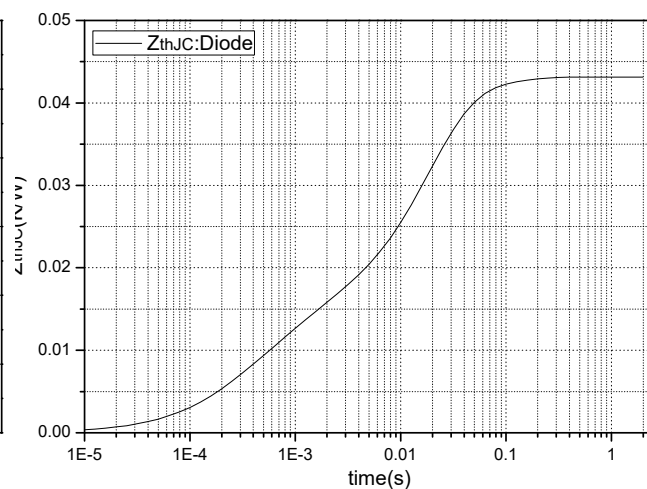
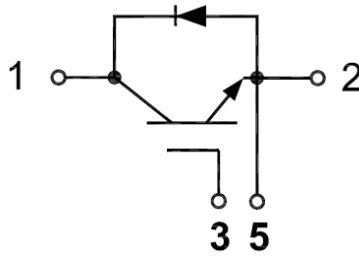


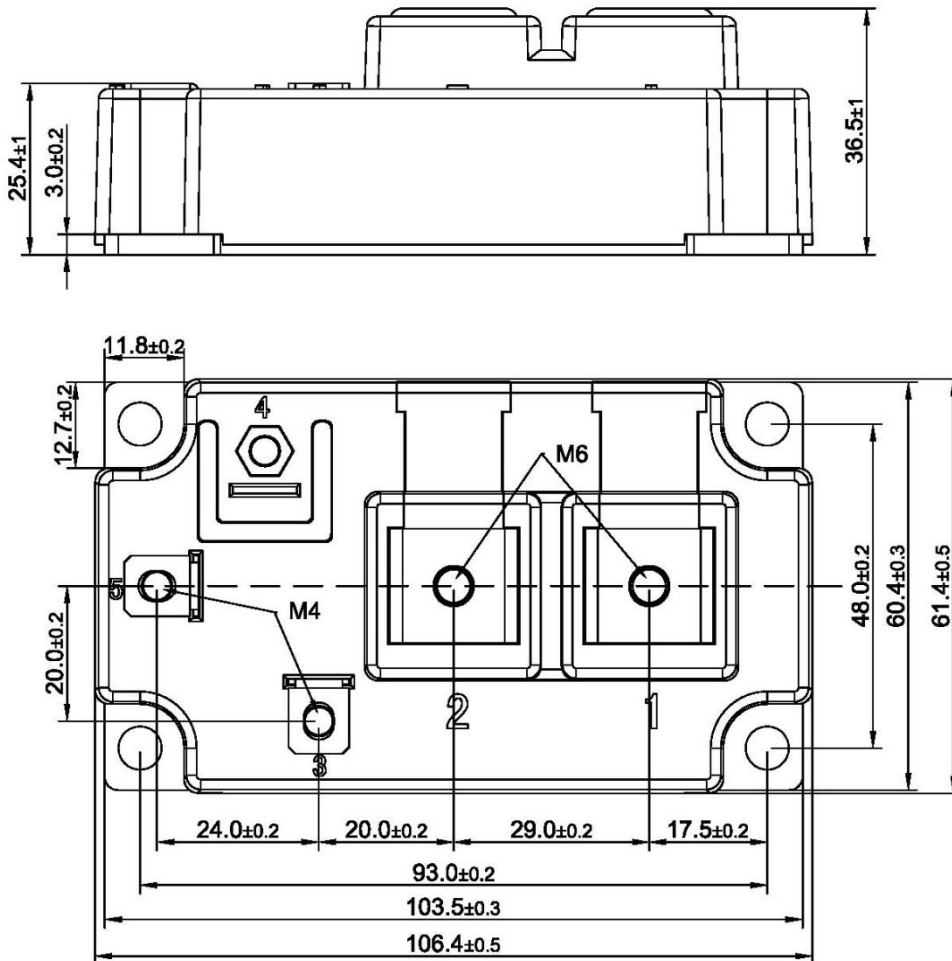
Fig.6 Transient Thermal Impedance (Diode)



Internal Circuit



Package Outline (Unit: mm):





Revision History

Date	Revision	Notes
05/29/2020	01	Initial Release

Announcement

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